



Latest developments of MCP detectors at Berkeley

*Oswald Siegmund, Jason McPhate,
Anton Tremsin and John Vallerga**

*Space Sciences Laboratory
U. California, Berkeley*

* jvv@ssl.berkeley.edu



Microchannel Plate Detectors

Where are they?

Recent MCP systems in Space based Astrophysics and Planetary Missions:

HST-COS, GALEX, LITES, JUNO, LRO-LAMP, Rosetta-ALICE, Pluto-ALICE, CHESS, FORTIS, SISTINE, ICON, GOLD, EMM-EMUS, SSULI, Solar Orbiter, SPICE, JUICE-UVS, INFUSE.

In progress:

SPRITE, MOBIUS, MANTIS, ASPERA, EUROPA-UVS, EUVST.

Proposals:

Cubesats, Rockets, MIDEX, PROBE.

Plus:

Neutron/X-ray beam lines, High Energy Physics, Synchrotron light sources



Microchannel Plate Detectors

How they work

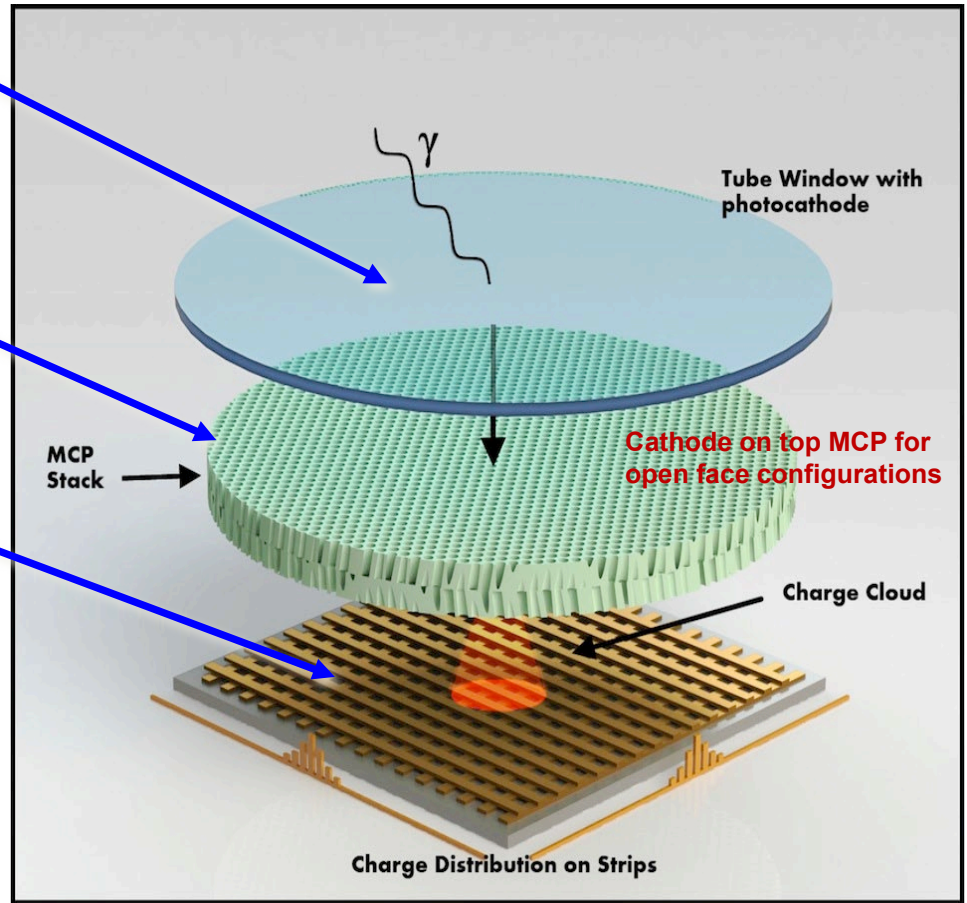
Photocathode converts photon to electron

Alkali halides, Multialkali, GaAs, GaN

MCP(s) amplify electron by 10^4 to 10^7

Patterned anode measures charge centroid

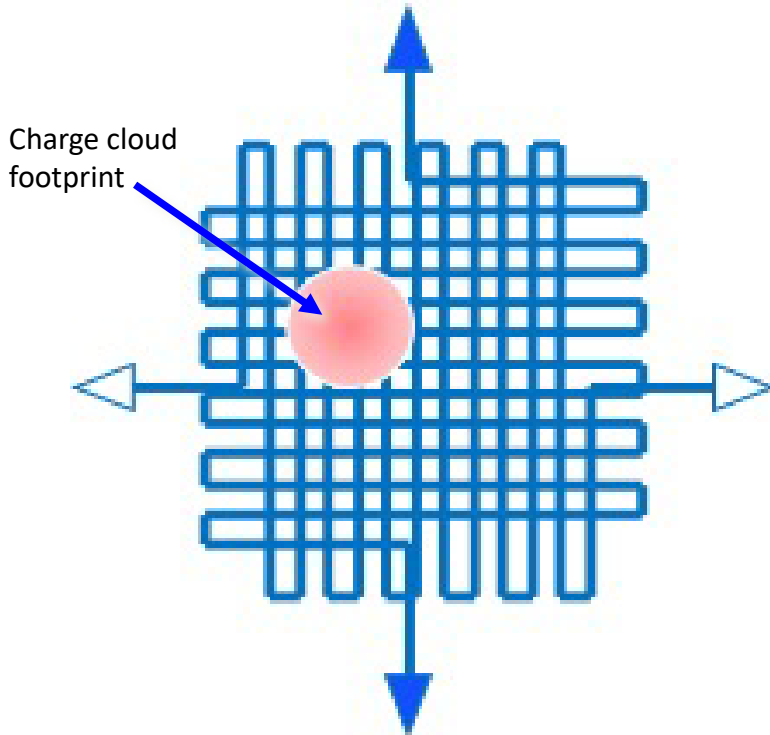
Cross strip, Cross delay line, Timepix ASIC or Phosphor.



Developments underway: Atomic layer deposited MCPs, large area borosilicate MCP substrates, cross strip and Timepix4 readouts, large area sealed tubes, and ASIC processing electronics

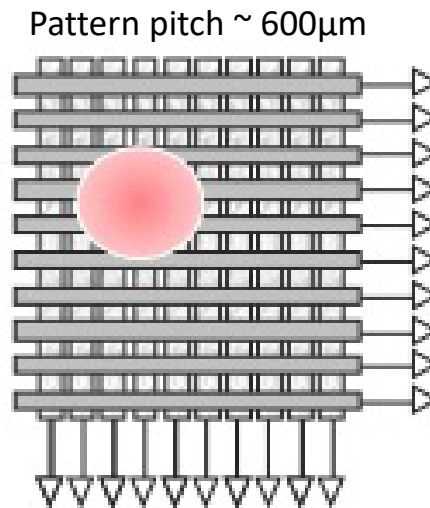


MCP readout anode types (partial list)



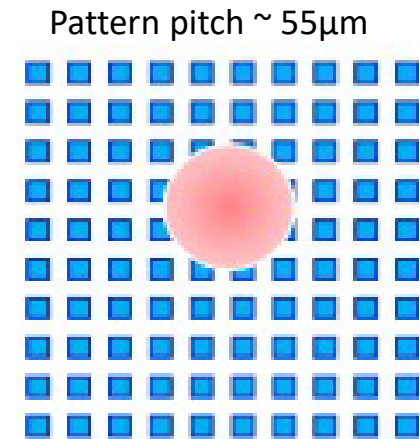
Cross Delayline (XDL)

4 amplifiers
Gain $\sim 10^7$
Rate $\sim 200\text{kHz}$



Cross Strip (XS)

2 x N amplifiers
Gain $\sim 10^6$
Rate $\sim 20\text{MHz}$



Timepix4 ASIC

512 x 448 amplifiers
Gain $\sim 50,000$
Rate $\sim 200\text{MHz per chip}$



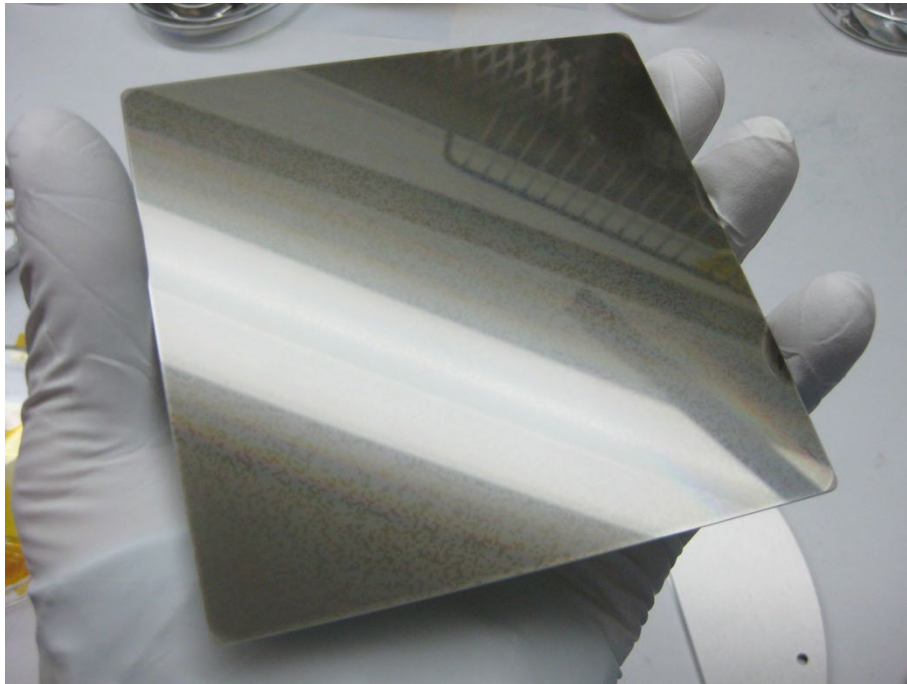
Large Area 10 μ m pore ALD MCPs

We are using 108mm ALD MCPs with 10 μ m pores for 5cm & 10cm XS tubes --- Incom has made 10 μ m pore MCPs as large as 20cm.

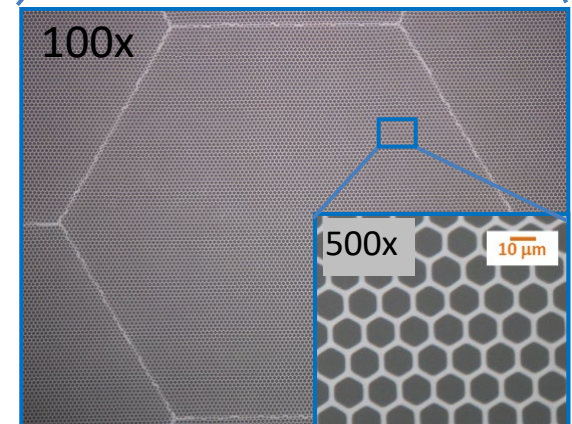
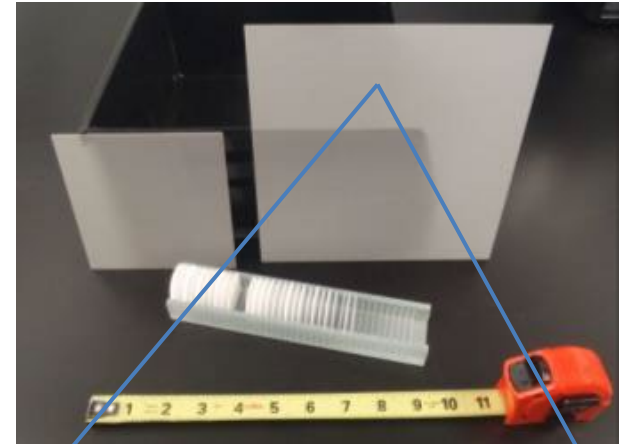
Borosilicate micro-capillary arrays (Incom, Inc.). Fabricated using hollow tubes (6 μ m, 10 μ m, or 20 μ m pores, 13° bias, l/d typically 60:1, open area ~73%) without etching. Separate resistive and secondary emissive layers are applied (ANL, Incom) using atomic layer deposition to function as MCPs.

- Large Areas, ---** --20 \times 20 cm² - 20 μ m & 10 μ m pores.
- Long Device Lifetimes, --** Stable gain to $>4 \times 10^{13}$ events cm⁻²
- Low γ -Ray Efficiency, --** $<0.7\%$ vs 2% (standard MCP) for MeV γ events
- Radiation hard, --** >100 kRad at nuclear reactor - no long term effects.
- Low Background, --** <0.05 events sec⁻¹ cm⁻², (<2 events pixel⁻¹ fortnight⁻¹)

203mm 10 μ m pore MCPs made. Borosilicate MCPs are very flat, stable compared to conventional MCPs. 20 μ m 208mm MCPs shaken >15 x, flown 4x with no failures (DEUCE, CU).



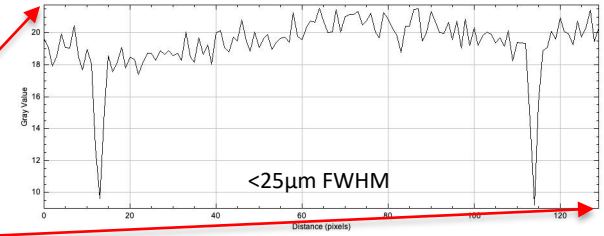
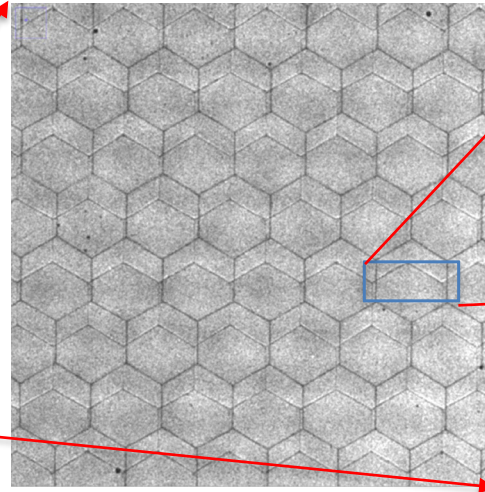
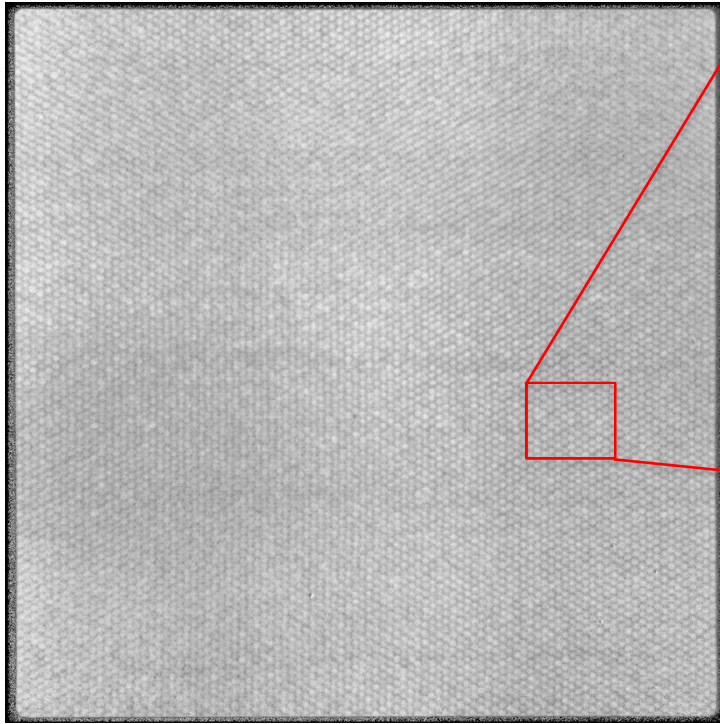
108mm format 10 μ m pore ALD-borosilicate substrate MCP.



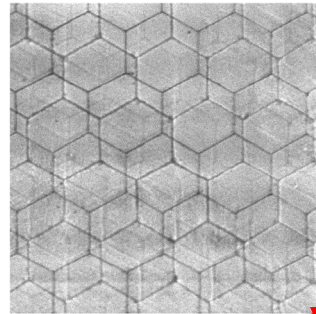


ALD 10 μ m Pore MCP Tests – XS Imaging

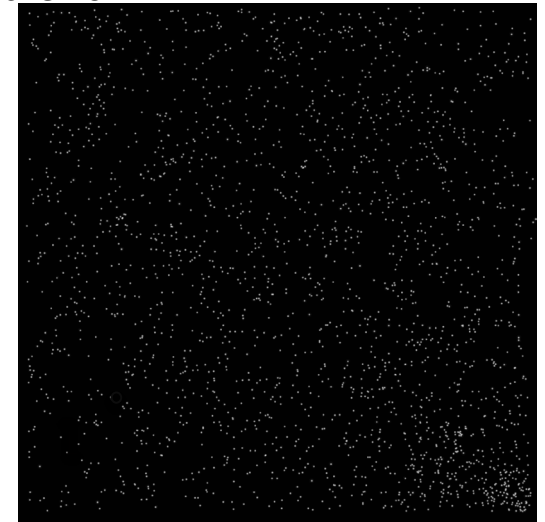
108 x 108mm Incom 10 μ m pore, 13 $^\circ$ bias, 70% OAR, L/D 60:1, MgO ALD chevron.
+ Csl cathode



54 x 54mm Incom 10 μ m pore, 13 $^\circ$ bias, 70% OAR, L/D 60:1, MgO ALD chevron.

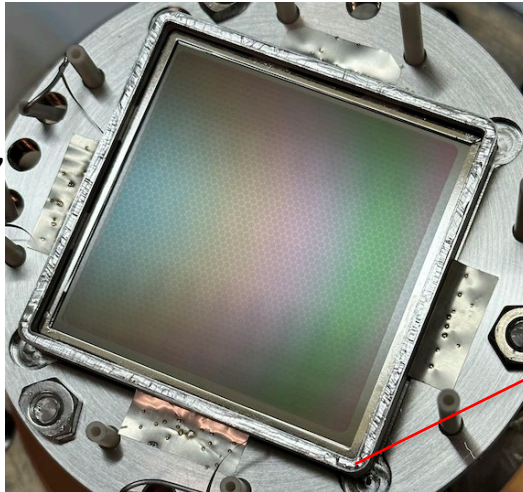


Similar behavior and performance



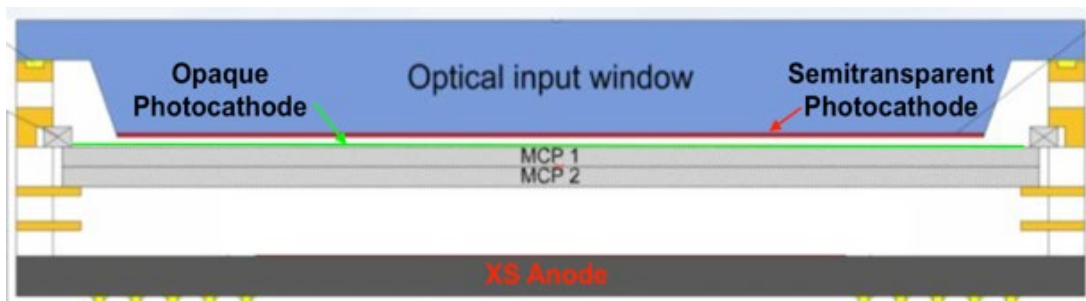
10cm, 10 μ m, ALD MCP Background
0.060 cts / sec / cm 2

CsI 54mm ALD,
MCP 10 μ m
Planacon



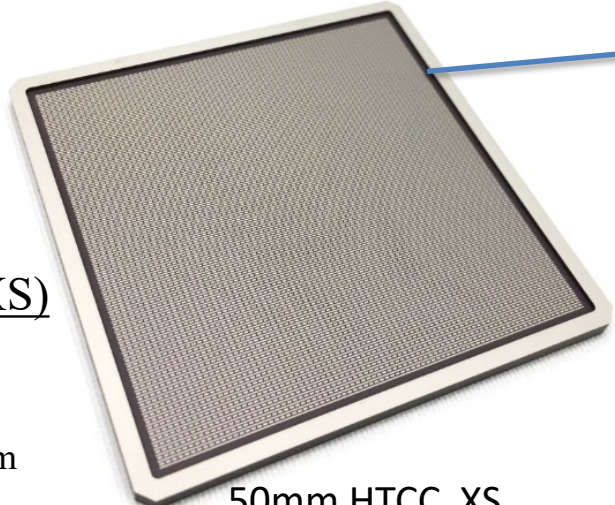


Cross Strip Readouts in Planacon Sealed Tubes

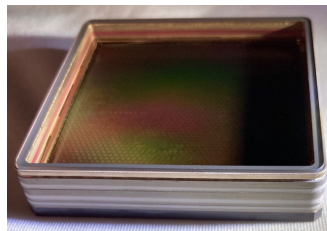


Cross section of a 100mm XS tube. UV input window can be coated with a bialkali cathode, or an opaque cathode can be used on the top MCP. A pair of 10 μm ALD MCPs provides signal amplification and an XS anode is the readout.

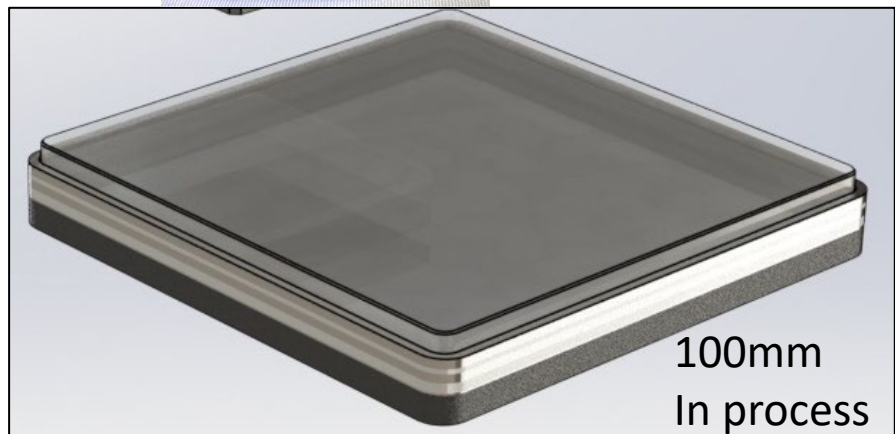
We have designed and are fabricating a 100mm format device with a UV window, a pair of 10 μm ALD MCPs and an XS anode readout. The techniques follow those used for the recent 50mm XS Planacon tubes.



50mm HTCC XS (High temperature co-fired ceramic).



Existing 50mm Planacon XS tube(s) & elevated to TRL 5/6



100mm In process

Cross- Strip (XS)

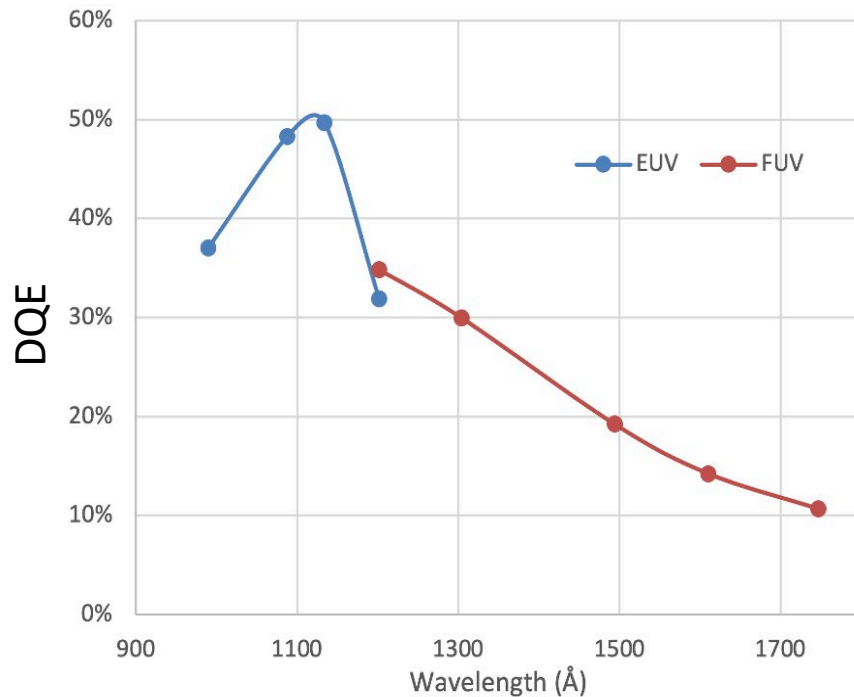
- Gain $\sim 10^6$
- Rate $< 5\text{MHz}$
- Size $\sim 1\text{cm}$ to 20cm
- Spatial resolution:
 - $\sim 15\mu\text{m}$ $< 5\text{cm}$
 - $\leq 25\mu\text{m}$ $\geq 10\text{cm}$



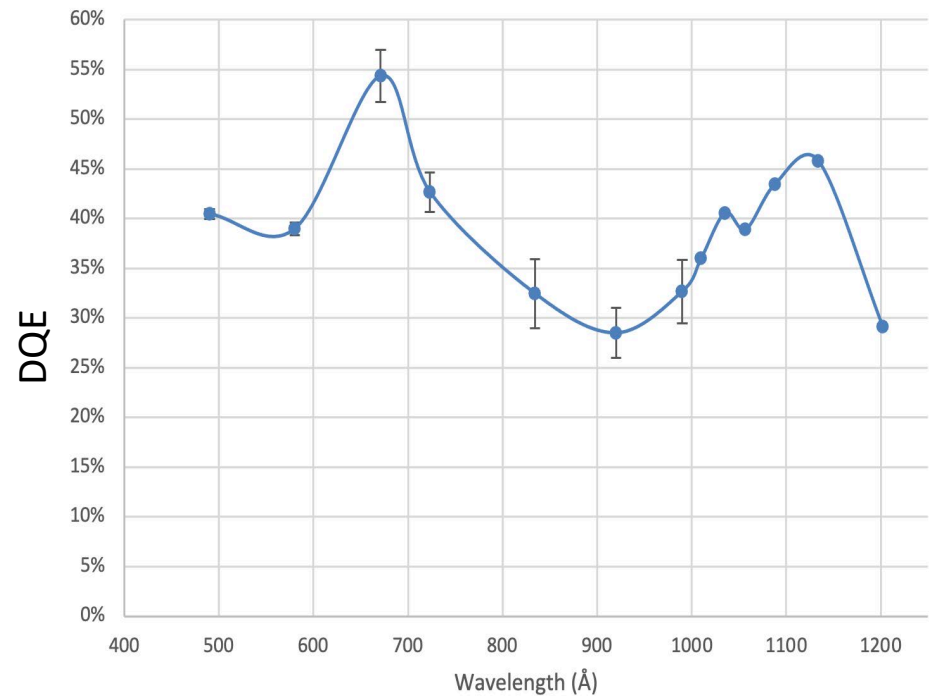
Opaque Photocathodes On ALD MCPs

Latest MCPs Demonstrate High DQE – Eg: CsI.

(bialkali & GaN for $>120\text{nm}$ – 350nm ,
KBr, KI, etc for 5nm – 100nm)



Recent CsI results (May 23) using $10\ \mu\text{m}$ pore MCP material show good QE results.

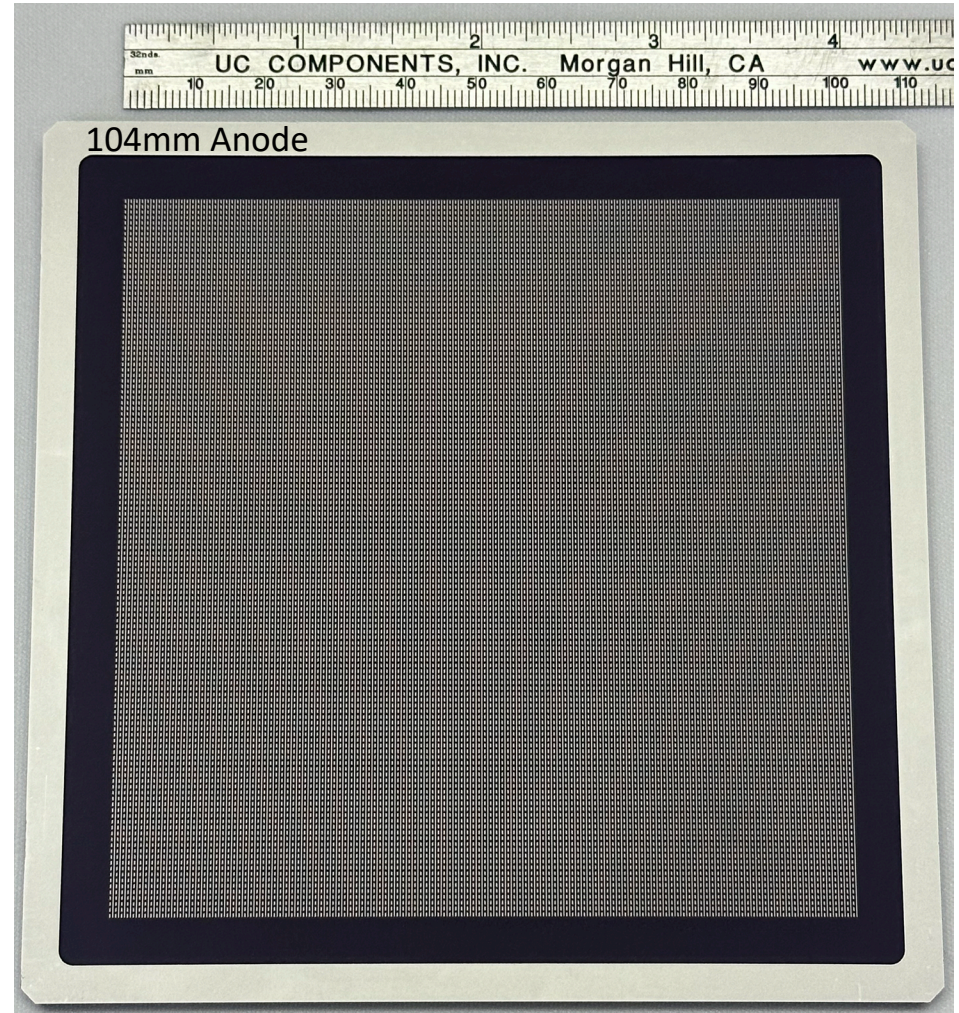
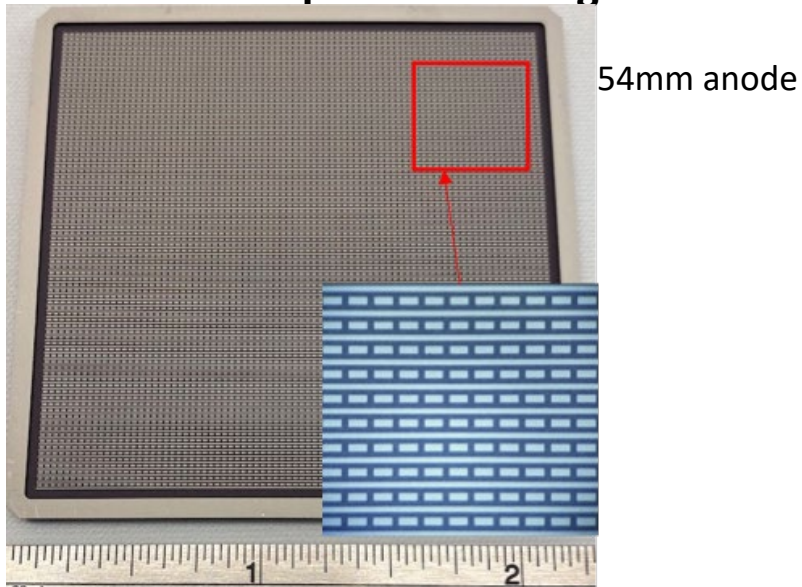


Recent results (Oct 23) using a different batch of $10\ \mu\text{m}$ pore MCP material also show very good QE results.

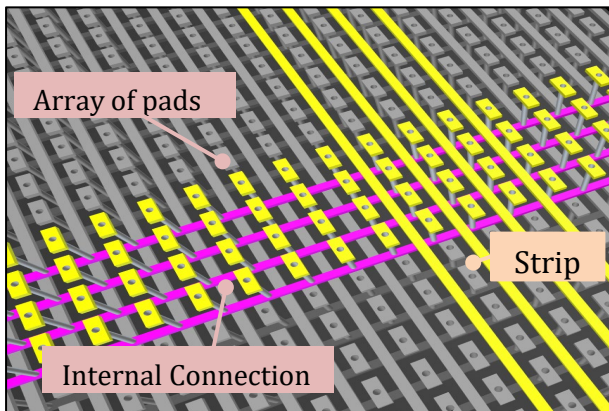


Cross Strip Anodes – HTCC (Ceramic)

High Temperature Cofired Ceramic (HTCC), 54mm & 104 mm square Cross Strip Anode. Designed in collaboration with Kyocera.



Anode active area has no open vias at all in this design using robust HTCC methodology. Design eliminates through holes and minimizes parasitic capacitance. Economical piece part cost even with tooling/setup costs. Long delivery, **just arrived**, 100mm XS anodes.

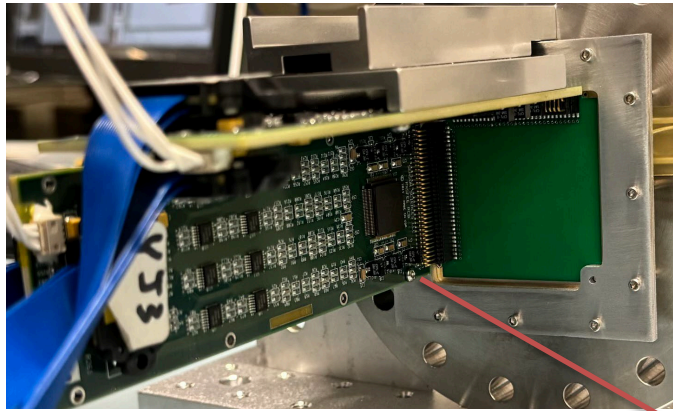


104mm Anodes currently in bench test, then will be used with MCPs in an open face detector for operational validation before making sealed tube(s). 9



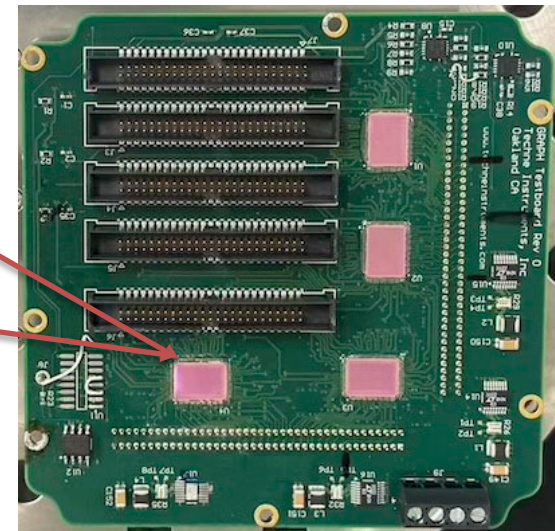
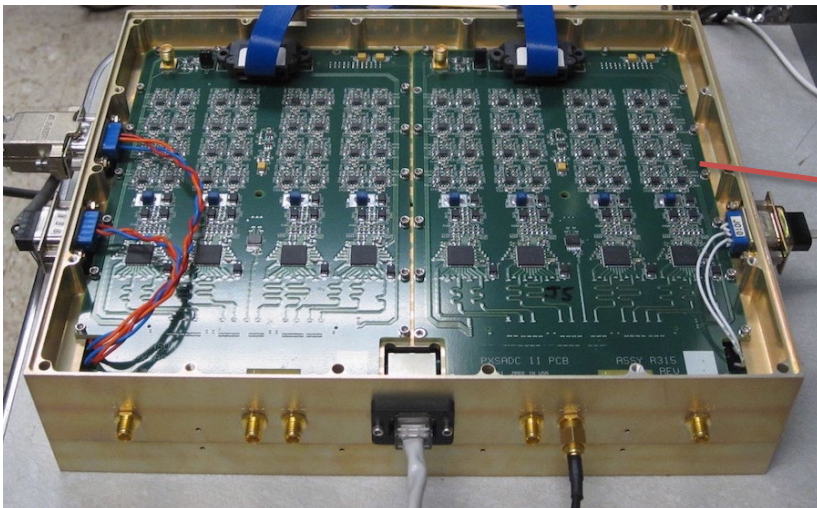
GRAPH - ASIC Electronics for XS Event Encoding

PXSII SMT amplifier



Earlier PXSII electronics has separate preamplifier boards and ADC/FPGA boards. Flown successfully on CHESS, INFUSE, 5x, but is bulky and heavy and draws 25w for a 50mm detector. We are implementing an ASIC version of the Cross Strip processing electronics – GRAPH. This implements charge sensitive amplifier (CSA) and fast ADC into single device, 46mW/channel, $\sim 7.4W = (2.4W + \text{FPGA power draw})$ for 50mm XS, $\sim 15W$ for 100mm XS. This has been prototyped and is being functionally tested and about to be used to process XY photon events on a 50mm XS detector.

PXSII SMT Digitizer and FPGA

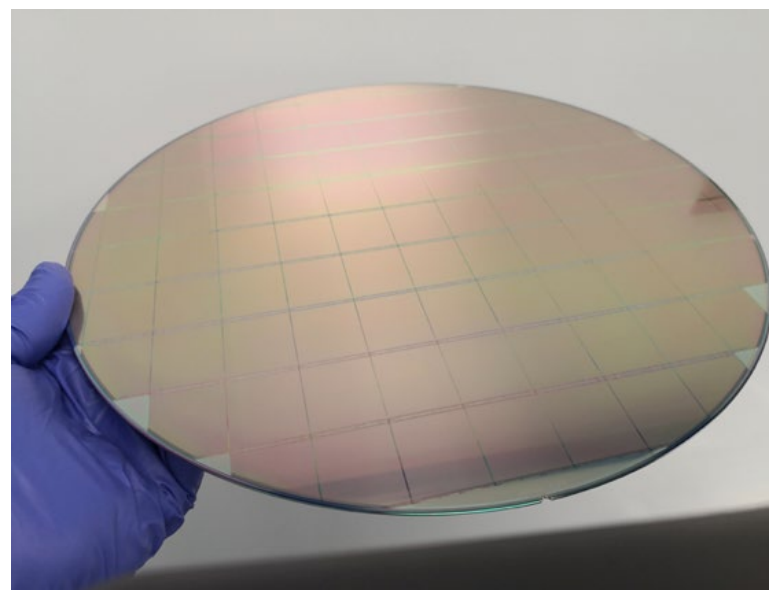


4x GRAPH test board, 16 channels per ASIC

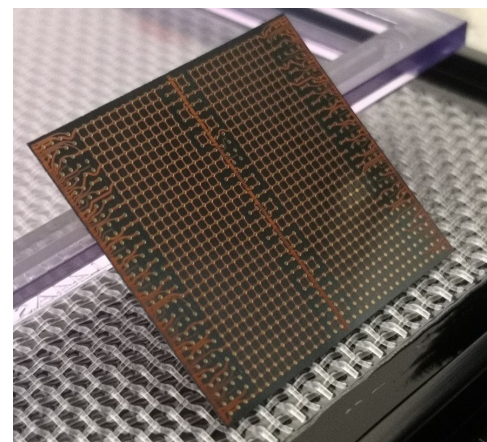


Timepix 4 – Mosaicing a pixelized MCP readout

- 512 x 448 pixelated readout ASIC (28x25mm) **Factor of 4 larger than Tpx3**
- **Large area tiling** using “Through Silicon Via” technology to bring signals to back of die (4-side abutable)
- Amplifier/ADC in each 55 μ m pixel
- Hit pixels measures both input amplitude and time of arrival
- 75e⁻ RMS noise for charge measurement
 - SNR > 100 allowing sub-pixel centroid accuracy
- Data-driven readout (shutterless)
- 2 Gigahits per second maximum output
- Designed by CERN Microelectronics Group



30cm TSMC CMOS wafer of Tpx4 dies

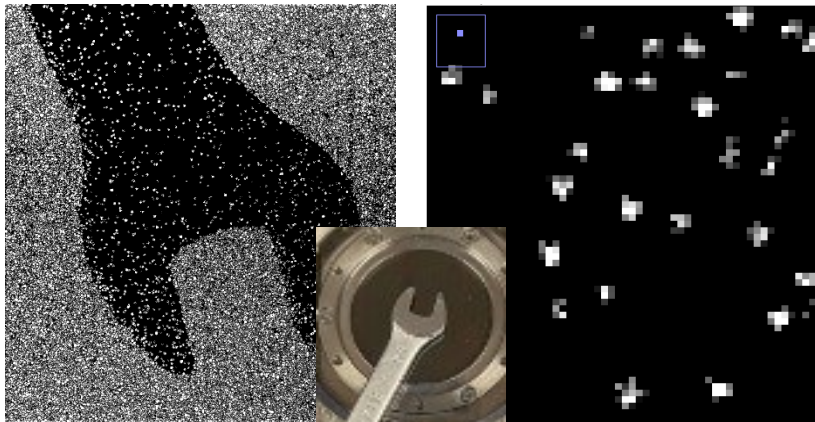


Backside BGA pattern – no wirebonds!

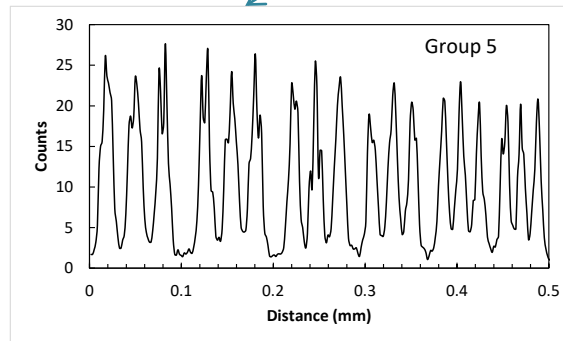
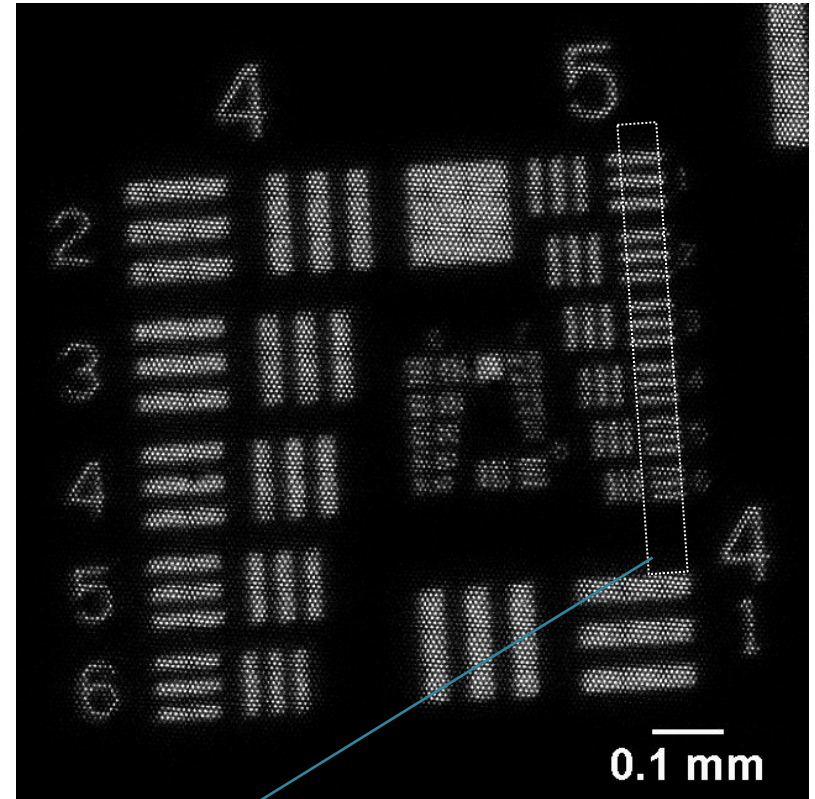


Timepix 4 – Advantages

- Extremely high resolution at low gain (lower HV and longer lifetime of MCP)
- Maintains performance when scaled to large area
- Huge dynamic range – Global 20 MHz event rate with centroiding
- Local pixel rate limit ~ 10 kHz, consistent with MCPs
- Data driven readout (photon counting)



First light - Tpx4 readout of MCP



USAF test pattern showing resolution better than 64lp/mm using Timepix readout



MCP detector developments for the next generation of space missions:

200mm 10 μ m MCP formats

Curved focal planes

High QE 100nm – 350nm

Low Flat field modulation

Improved MCP gain stability

Low background rates ---

Low radiation sensitivity

Large XS readout formats

Open face and sealed tubes

Spatial resolution $\leq 25\mu$ m FWHM

High performance electronics
with low power/volume /mass

Up to 200mm demonstrated

Cylindrical demonstrated

>50% CsI demonstrated, Bialkali 30% @
180nm, 360nm cutoff

ALD MCPs $\leq 20\%$ hex pattern ~ 1 resel wide

$> 5 \times 10^{13}$ events cm^{-2} demonstrated

$< 0.06 \text{ cm}^{-2}\text{s}^{-1}$ demonstrated up to 20cm

Achieve 0.7 % MeV gamma efficiency

100mm demonstrated, 200mm possible

Up to 100mm open face, 50mm Planacon XS
demonstrated, **100mm sealed tubes in progress.**

100mm format demonstrated

GRAPH ASIC in development for XS anodes
Tpx4 ROIC as scalable high performance anode



Backup Slides

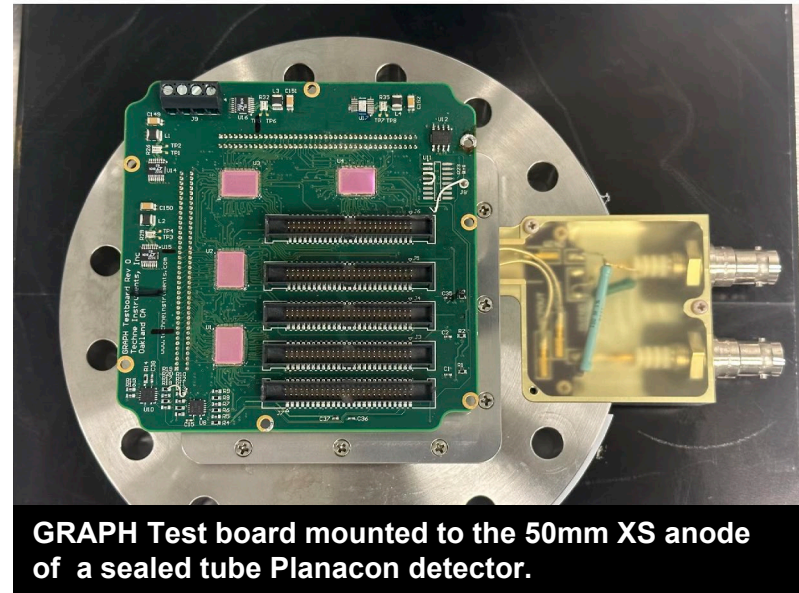
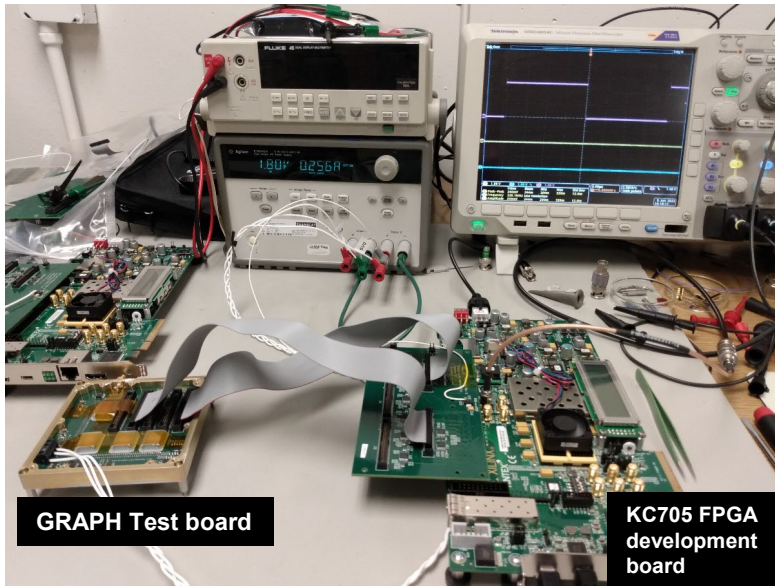


Testing of the GRAPH ASIC for Processing Photon Event Positions on Cross Strip Anodes

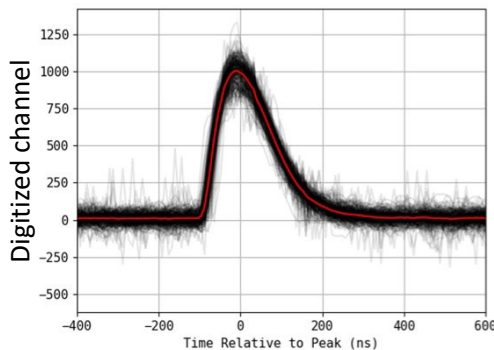
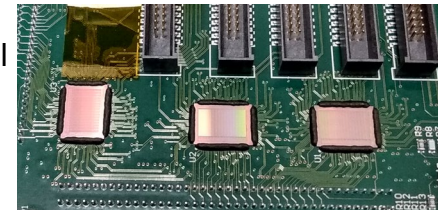
#2365

- Firmware has been commissioned for multi-ASIC readout & high-speed Ethernet data interface.
- Python-based S/W for scriptable testing and large dataset aggregation is also implemented.

Initial test functionality and FW/SW development setup.



- First generation ASICs are wire bonded directly to test boards to give a 32 channel X and 32 channel Y capability
- Test boards can be mounted directly to anode / detector backplane, and then to an FPGA board behind that.

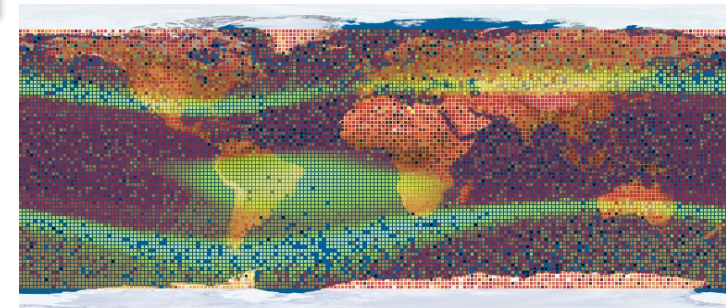
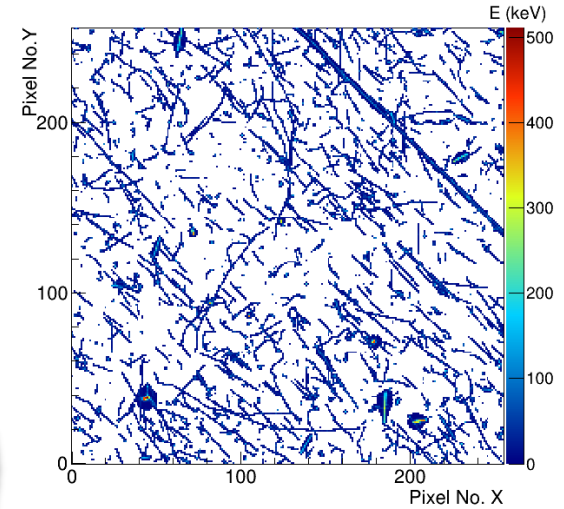
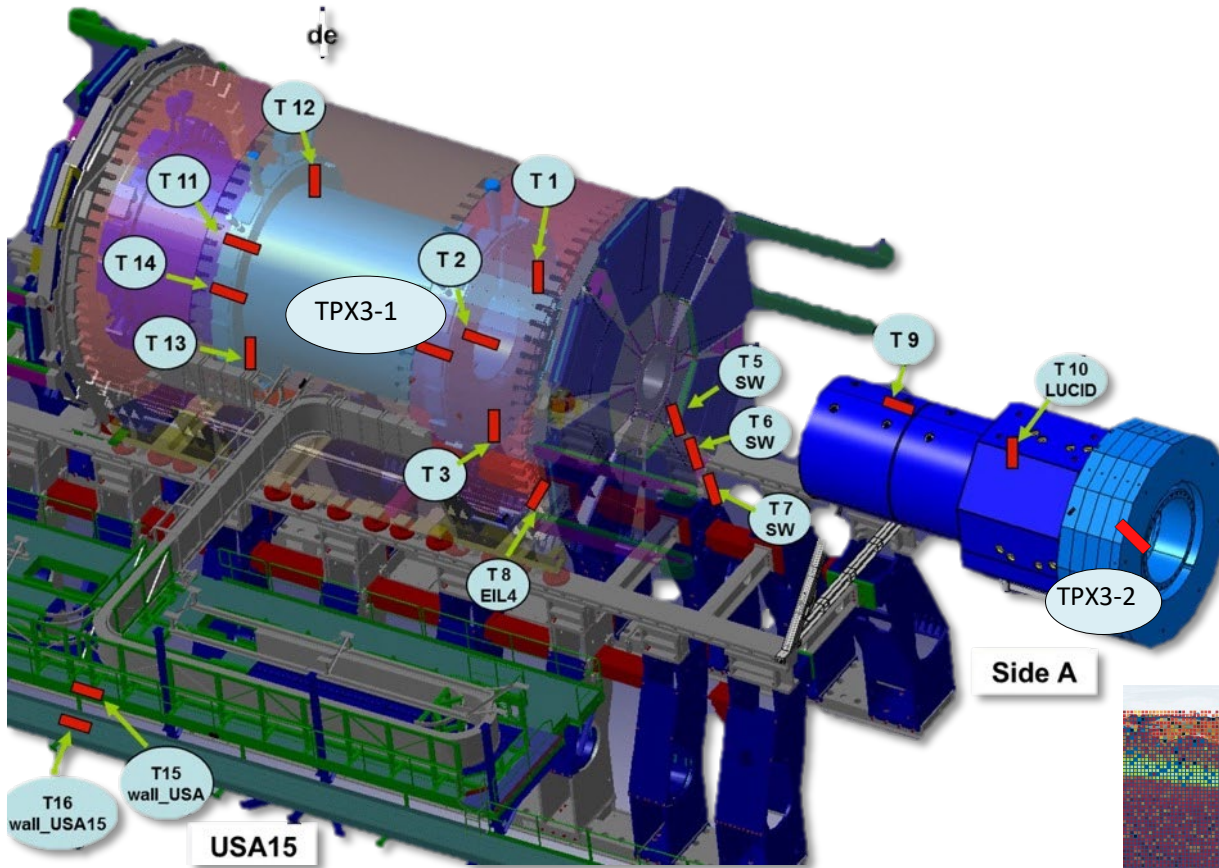


Charge injection input: $\sim 50\text{fC}$ pulse.
 Output: ~ 250 trace captures, average trace overlaid (red) equates to ~ 1000 ADC counts, $\sim 300\text{e}^-/\text{ADC count}$. Typical peak for MCP signals @ $\sim 2 \times 10^6$ gain spread over 5-7 XS strips.

Custom ASIC implements charge sensitive amplifier (CSA) and fast ADC into single 16 channel device, 11 x 9 mm size. 46mW/channel, $\sim 7.4\text{W} = (2.4\text{W} + \text{FPGA power draw})$ for 50mm XS Planacon, $\sim 15\text{W}$ for 100mm XS. 160ns CSA return to baseline allows high counting rates ($\sim 10\%$ deadtime at 6MHz). Multi-photon recognition and processing algorithms should increase this substantially.



Radiation tolerance



Location of Timepix detectors in LHC - ATLAS

B. Bergmann *et al.*, "Relative luminosity measurement with Timepix3 in ATLAS", *JINST* **15** C01039, 2020.

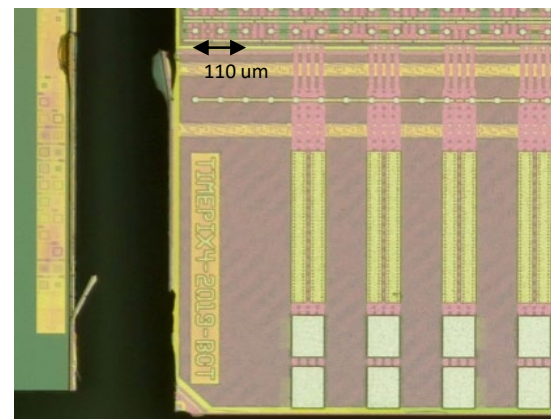
Dose distribution in orbit measured with SATRAM. From:

<https://satram.utef.cvut.cz>

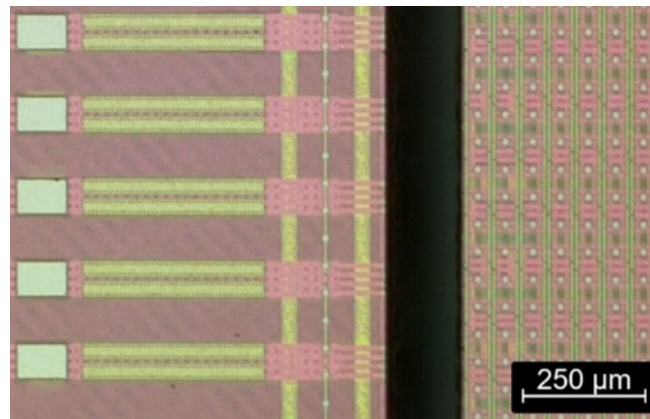


Stealth Dicing tests

- To minimize gaps between ASICs and therefore better event centroids at these interfaces, the ASIC dicing from the wafer must be very accurate and reproducible.
- Stealth Laser dicing uses a focused laser beam to modify the Si crystal structure, making it weaker, so when the wafer is stretched, it naturally cleaves at these laser defined boundaries. Front side laser ablation is used first in order to reduce meandering related to metal layers separation.
- Experiments with actual Tpx4 wafer fragments showed clean, debris free edges estimated to be rough at 10 microns, sufficient for 55 μ m spacing between ASIC dies.



#1. First test of Si Stealth dicing. Very accurate silicon cleaving but top metal surface shows “meandering” and therefore must be removed first with laser ablation.



#2. Second test of Si Stealth dicing, this time with laser ablation of metal layers. Test was a success!. Clean cuts estimated to be rough to 10 microns, a small fraction of a 55 μ m pixel (seen on right)